



TET ESTEL AS
ESTONIA

**June
2013**

**Series
D553-800**

**Rectifier Press-Pack
Diode
Type D553-800**

Designed for rectifiers and industrial applications

Maximum mean forward current	I _{FAV}	800 A							
Maximum repetitive peak reverse voltage	U _{RRM}	4400 ÷ 6000 V							
Reverse recovery time	trr (typ)	60 µs							
U _{RRM} , V	4400	4600	4800	5000	5200	5400	5600	5800	6000
Voltage code	44	46	48	50	52	54	56	58	60
Tvj, °C					- 60 ÷ 150				

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	D553-800	Conditions
I _{FAV}	Mean forward current	A	800 1700	Tc=120 °C, Tc=55 °C, 180° half-sine wave, 50 Hz
I _{FRMS}	RMS forward current	A	1255	Tc=120 °C
I _{FSM}	Surge forward current	kA	16 18	Tvj=150°C Tvj=25°C
I ² t	Limiting load integral	kA ² s	1280 1620	Tvj=150°C Tvj=25°C
U _{RRM}	Repetitive peak reverse voltage	V	4400÷6000	Tj min≤Tvj≤TjM 180° half-sine wave, 50 Hz
U _{RSR}	Non-repetitive peak reverse voltage	V	4500÷6100	Tj min≤Tvj≤TjM 180° half-sine wave tp=10 ms, Single pulse
T _{stg}	Storage temperature	°C	-60÷80	
T _{vj}	Junction temperature	°C	-60÷150	

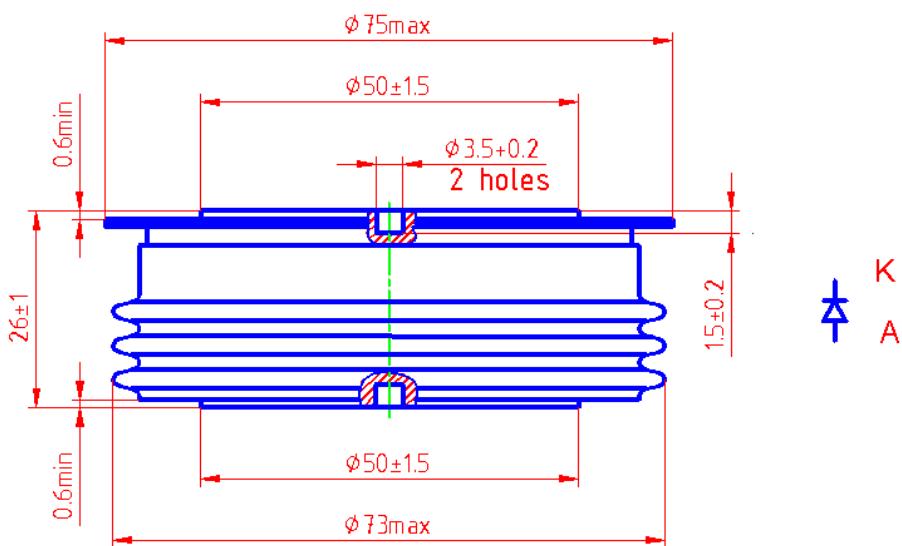
CHARACTERISTICS

U _{FM}	Peak forward voltage	V	1,85	Tvj=25°C, I _{TM} =3,14 I _{FAV}
U _{F(TO)}	Threshold voltage	V	1,05	Tvj=150°C 1,57 I _{FAV} < I _T <4,71 I _{FAV}
R _T	Forward slope resistance	mΩ	0,41	
I _{RRM}	Repetitive peak reverse current	mA	100	Tvj=150°C, UR= U _{RRM}

CHARACTERISTICS				
Symbols and parameters		Units	D553-800	Conditions
Qrr	Recovered charge (typ)	µC	6000	Tvj=150°C If=800A diR/dt =10 A/µs UR=100V
trr	Reverse recovery time (typ)	µs	60	
Irrm	Peak reverse recovery current (typ)	A	200	
Rthjc	Thermal resistance junction to case	°C/W	0,02	

ORDERING				
	D	553	800	56
	1	2	3	4

1. Diode
2. Design version
3. Mean forward current, A
4. Voltage code (56=5600 V)



Mounting force : 19 ÷ 28 kN
Weight : 580 grams